

Listing of claims:

1. **(Previously presented)** A composition for the production of semiconductors, comprising H_2SiF_6 and/or HBF_4 in a total amount of 10-500 mg/kg, 12-17% by weight of H_2SO_4 , 2-4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution.
2. **(Previously presented)** A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a composition comprising H_2SiF_6 with the structured semiconductor surface in order to remove residual polymers from the structured semiconductor surface.
3. **(Previously presented)** A process according to claim 2 for the removal of residual polymers from Al or Al-containing conductor tracks on said semiconductor surface.
4. **(Previously presented)** A process according to claim 2 for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.
5. **(Previously presented)** A process for the removal of residual polymers from aluminum or copper/aluminum alloys comprising contacting a semiconductor surface having aluminum or copper/aluminum alloys with a composition according to claim 1.
6. **(Previously presented)** A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a composition comprising H_2SiF_6 and/or HBF_4 in a total amount of 10-500 mg/kg, 12-17% by weight of H_2SO_4 , 2-4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution.

7. **(Previously presented)** A process according to claim 2 further comprising contacting a semiconductor surface with a composition comprising H_2SiF_6 in a spin etcher or in a tank unit.

8. **(Previously presented)** A process for the removal of residual polymers from Al or Al-containing conductor tracks, wherein residual polymers are removed using a composition according to claim 1.

9.-10. **(Cancelled)**

11. **(Previously presented)** A process according to claim 6, for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.

12. **(Cancelled)**

13. **(Cancelled)**

14. **(Previously presented)** The process of claim 2, wherein said composition further comprises HBF_4 .